

	GaN	MOSFET [1]
Power	1	0.6
Current	1	0.75
Junction temp	0.8	0.8
G-S Voltage [2]	1	0.6
D-S Voltage	1	0.75
SEE	1	n/a
TID	1	n/a
Neutron	1	n/a

Note: All EPC GaN devices are 100% tested at 120% of maximum drain source and gate-source voltage.

[1] MOSFET derating based on EEE-INST-002

[2] GaN devices should be operated with on state gate voltage greater than 4.2 V